

ON THE POSSIBLE INTENSIFICATION
OF DISINTEGRATION OF A SOLID
SOLUTION OF OXYGEN UNDER ULTRASONIC
TREATMENT OF SPECIMENS OF SILICON

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S u m m a r y

By triple-crystal diffractometry, a comparative study of the scattering of X-ray emission by annealed specimens after ultrasonic treatment and by reference Cz-Si crystals after their analogous annealing at temperatures 850–1050 °C is performed. The corresponding sizes and concentrations of the clusters of point defects and dislocation loops created in the processes of disintegration of a solid solution of oxygen and clusterization.